

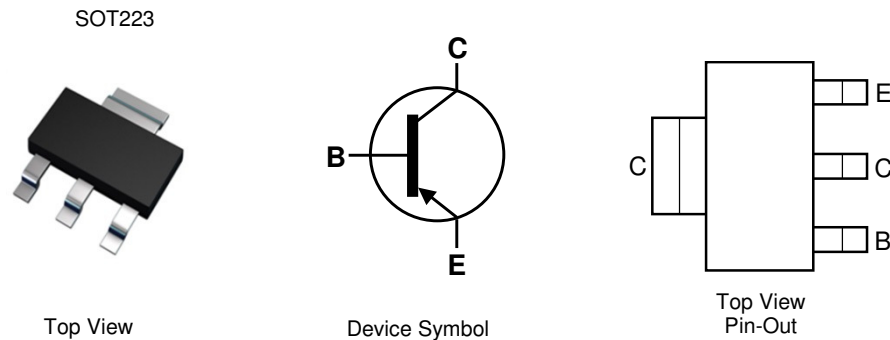
**300V PNP HIGH VOLTAGE TRANSISTOR IN SOT223**

**Features**

- $BV_{CEO} > -300V$
- $I_C = -0.5A$  Continuous Current
- $I_{CM} = -1A$  Peak Pulse Current
- Complementary NPN Type: FZT657
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208③
- Weight: 0.112 grams (Approximate)

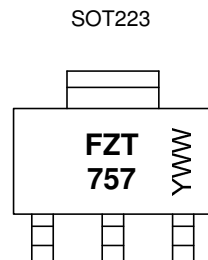


**Ordering Information** (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT757TA	AEC-Q101	FZT757	7	12	1,000

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-Free, "Green" and Lead-Free.
  3. Halogen- and Antimony-Free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



FZT 757 = Product Type Marking Code  
 YWW = Date Code Marking  
 Y or  $\bar{Y}$  = Last Digit of Year (ex: 5= 2015)  
 WW or  $\bar{W}W$  = Week Code (01~53)

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-300	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-300	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Continuous Collector Current	I <sub>C</sub>	-0.5	A
Peak Pulse Current	I <sub>CM</sub>	-1	A

**Thermal Characteristics** (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

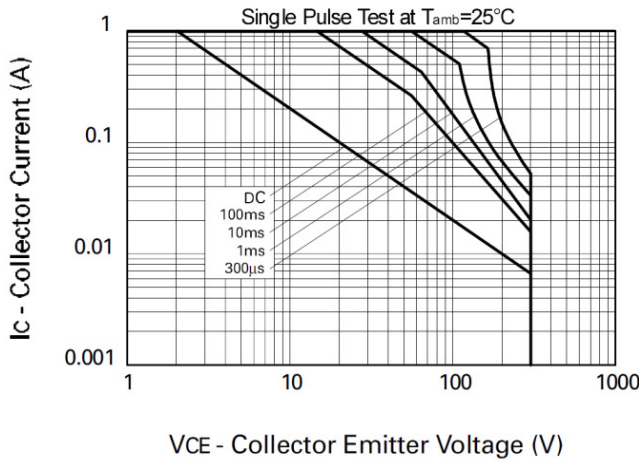
Characteristic	Symbol	Value	Unit
Power Dissipation	P <sub>D</sub>	(Note 5)	3.0
		(Note 6)	2.0
		(Note 7)	1.6
		(Note 8)	1.2
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	(Note 5)	41.7
		(Note 6)	62.5
		(Note 7)	78.1
		(Note 8)	104
Thermal Resistance, Junction to Leads	R <sub>θJL</sub>	12.9	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 10)

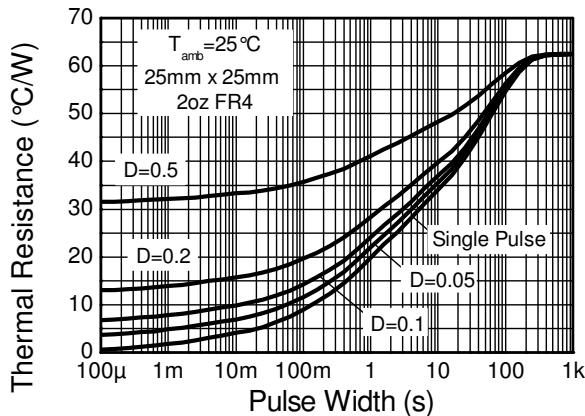
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  - Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
  - Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
  - Same as Note 5, except the device is mounted on minimum recommended pad layout.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

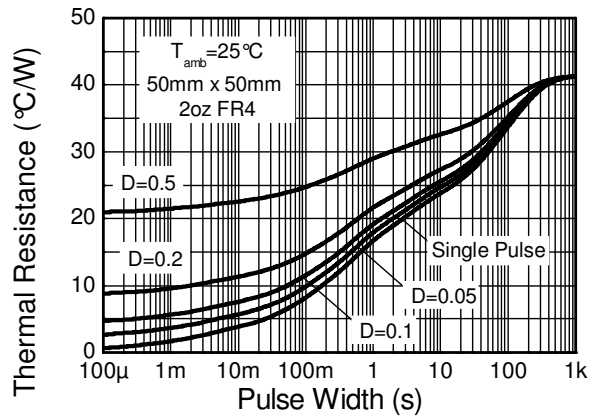
**Thermal Characteristics and Derating Information**



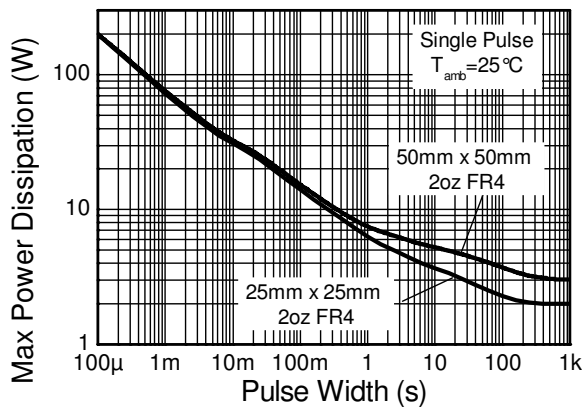
**Safe Operating Area**



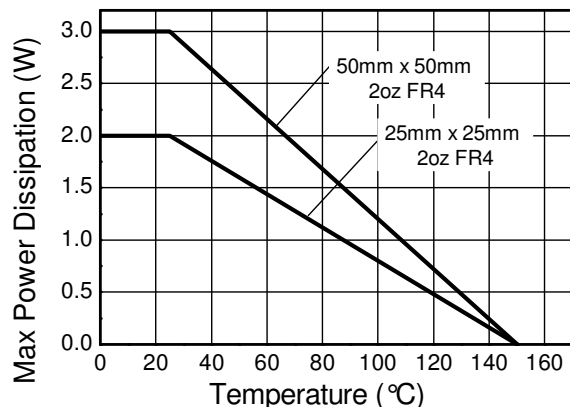
**Transient Thermal Impedance**



**Transient Thermal Impedance**



**Pulse Power Dissipation**



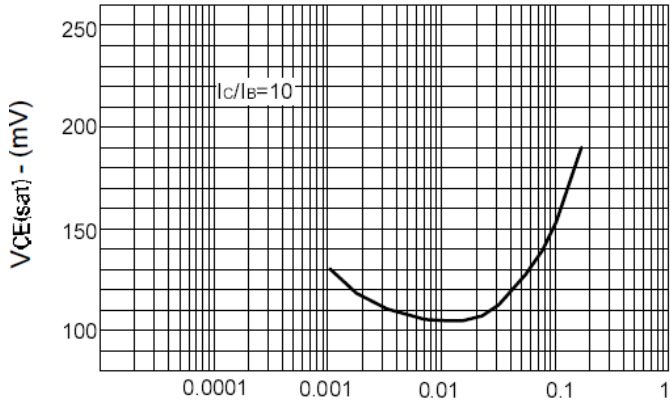
**Derating Curve**

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-300	–	–	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV <sub>CEO</sub>	-300	–	–	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	–	–	V	I <sub>E</sub> = -100μA
Collector Cut-Off Current	I <sub>CBO</sub>	–	<1	-100	nA	V <sub>CB</sub> = -200V
Emitter Cut-Off Current	I <sub>EBO</sub>	–	<1	-100	nA	V <sub>EB</sub> = -5.6V
Collector-Emitter Saturation Voltage (Note 11)	V <sub>CE(sat)</sub>	–	–	-0.5	V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Base-Emitter Saturation Voltage (Note 11)	V <sub>BE(sat)</sub>	–	–	-1.0	V	I <sub>C</sub> = -100mA, I <sub>B</sub> = -10mA
Base-Emitter Turn-On Voltage (Note 11)	V <sub>BE(on)</sub>	–	–	-1.0	V	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -5V
DC Current Gain (Note 11)	h <sub>FE</sub>	40	–	–	–	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5V
		50	–	–		I <sub>C</sub> = -100mA, V <sub>CE</sub> = -5V
Current Gain-Bandwidth Product	f <sub>T</sub>	30	–	–	MHz	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -20V, f = 20MHz
Output Capacitance	C <sub>obo</sub>	–	–	20	pF	V <sub>CB</sub> = -20V, f = 1MHz

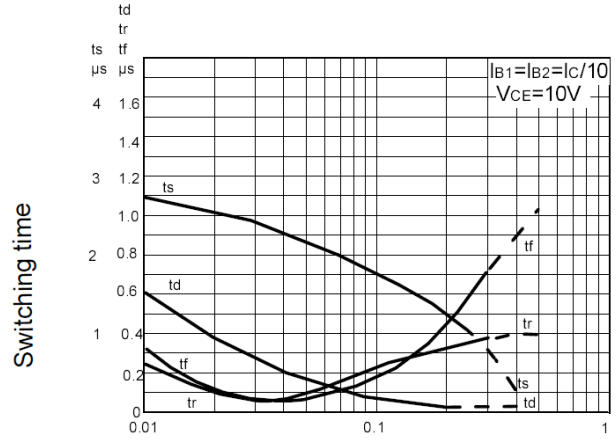
Note: 11. Measured under pulsed conditions. Pulse width ≤ 300 μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)



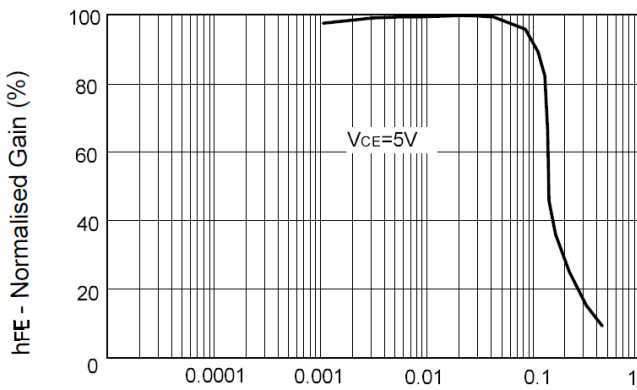
IC - Collector Current (Amps)

**VCE(sat) v IC**



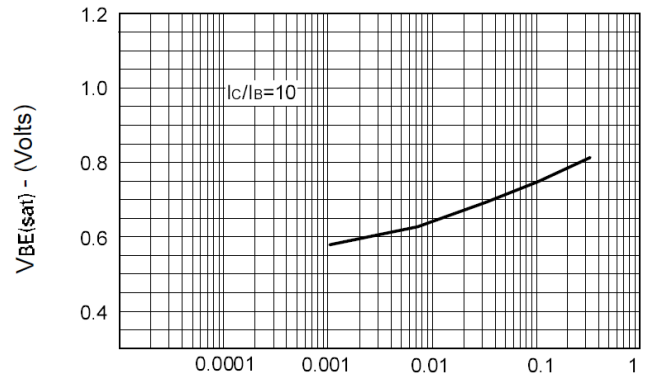
IC - Collector Current (Amps)

**Switching Speeds**



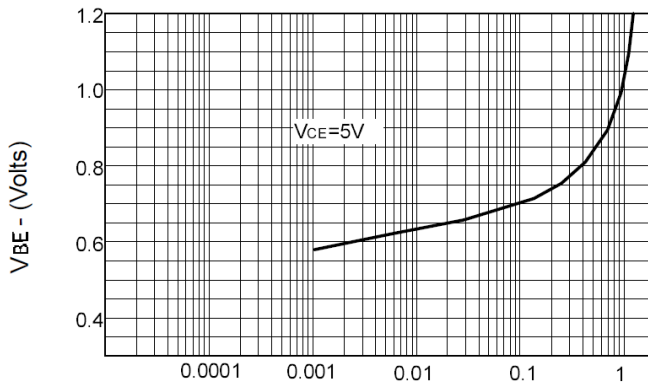
IC - Collector Current (Amps)

**hFE v IC**



IC - Collector Current (Amps)

**VBE(sat) v IC**

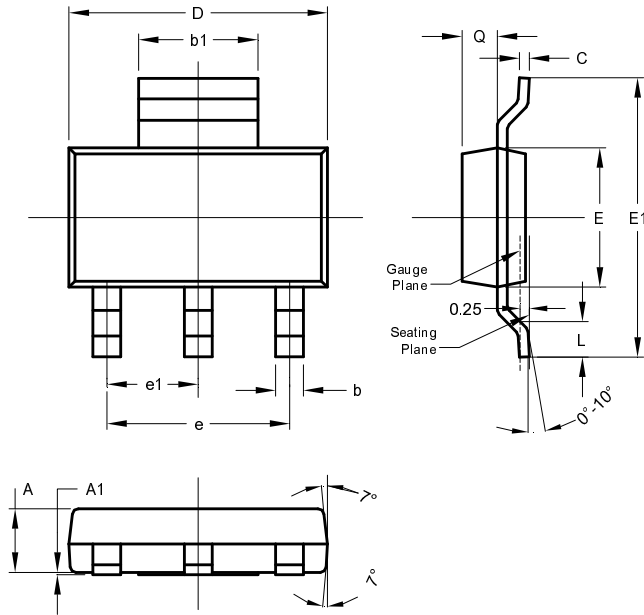


IC - Collector Current (Amps)

**VBE(on) v IC**

**Package Outline Dimensions**

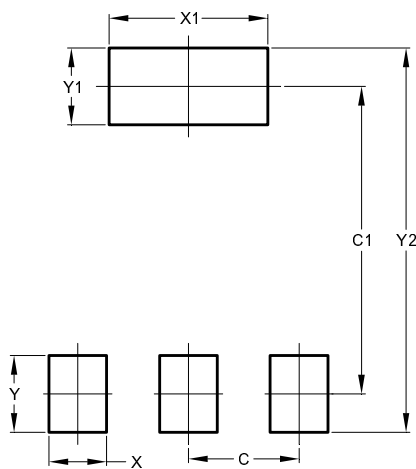
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.

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